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38327	7590 06/26/2006		EXAMINER	
REED SMITH LLP 3110 FAIRVIEW PARK DRIVE, SUITE 1400 FALLS CHURCH, VA 22042			GIESY, ADAM	
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Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Annlinent/e)
	Application No.	Applicant(s)
Office Action Commence	10/082,314	ISSHIKI, FUMIO
Office Action Summary	Examiner	Art Unit
	Adam R. Giesy	2627
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence address
A SHORTENED STATUTORY PERIOD FOR REPLY WHICHEVER IS LONGER, FROM THE MAILING DA  - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication.  - If NO period for reply is specified above, the maximum statutory period w  - Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be tim vill apply and will expire SIX (6) MONTHS from cause the application to become ABANDONEI	N. sely filed the mailing date of this communication. (35 U.S.C. § 133).
Status		
1) ☐ Responsive to communication(s) filed on <u>08 Ju</u> 2a) ☐ This action is <b>FINAL</b> . 2b) ☐ This      3) ☐ Since this application is in condition for alloware closed in accordance with the practice under Example 2.	action is non-final. nce except for formal matters, pro	
Disposition of Claims		
4)  Claim(s) 1-18 is/are pending in the application.  4a) Of the above claim(s) is/are withdray  5)  Claim(s) is/are allowed.  6)  Claim(s) 1,3-5,7,8,11 and 14-18 is/are rejected.  7)  Claim(s) 9,10,12 and 13 is/are objected to.  8)  Claim(s) are subject to restriction and/o  Application Papers  9)  The specification is objected to by the Examine  10)  The drawing(s) filed on 26 February 2002 is/are  Applicant may not request that any objection to the  Replacement drawing sheet(s) including the correct  11)  The oath or declaration is objected to by the Examine	vn from consideration.  I.  r election requirement.  r.  e: a)⊠ accepted or b)□ objected or by	e 37 CFR 1.85(a). jected to. See 37 CFR 1.121(d).
Priority under 35 U.S.C. § 119		
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of:  1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority application from the International Bureau * See the attached detailed Office action for a list	s have been received. s have been received in Applicati rity documents have been receive u (PCT Rule 17.2(a)).	on No ed in this National Stage
Attachment(s)  1) Notice of References Cited (PTO-892)  2) Notice of Draftsperson's Patent Drawing Review (PTO-948)  3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:	

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#### **DETAILED ACTION**

## Specification

1. The title of the invention is not descriptive. A new title is required that is clearly indicative of the invention to which the claims are directed.

The following title is suggested: Optical Disc Drive Apparatus With a Semiconductor Laser Containing an Asymmetric Quantum Well Structure.

## Claim Objections

2. Claim 14 is objected to because of the following informalities:

Examiner suggests that the phrase "...wherein a d.c. drive..." should read "...wherein a d.c. (direct current) drive...".

Appropriate correction is required.

3. Claim 16 is objected to because of the following informalities:

Examiner asserts that the phrase "...claim 1, comprising and a waveband..." should read "...claim 1, comprising a waveband ...".

Appropriate correction is required.

#### Claim Rejections - 35 USC § 103

- 4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 5. Claims 1, 3-5, 7, 8, 14, and 18 are rejected under 35 U.S.C. 103(a) as being unpatentable over Yoshida et al. (hereinafter Yoshida US Doc. No. 2002/0024153 A1)

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in view of Valster et al. (hereinafter Valster – US Pat. No. 5,296,717) and further in view of Sundaram et a. (hereinafter Sundaram – US Doc. No. 2004/0195509 A1).

Regarding claim 1, Yoshida discloses an optical head comprising a light source for emitting a light beam (Figure 3, element 301), a lens for focusing the light beam onto a medium (element 302), and a detector for detecting a reflected light beam from the medium (311), the light source having an active layer that is an indirect semiconductor (see page 4, paragraphs 0040-0042). Yoshida fails to disclose that the laser has a barrier layer or that the semiconductor layer contains quantum wells.

Valster discloses an indirect semiconductor laser wherein the light source comprises a semiconductor laser comprising an active layer and a barrier layer (see abstract), said active layer being an indirect semiconductor (see abstract), said indirect semiconductor having a disordered quantum well structure (column 6, lines 38-40). Valster fails to specifically disclose that the quantum well structure is asymmetric.

Sundaram discloses an indirect semiconductor device that contains quantum wells in which the quantum wells are asymmetric (see page 3, paragraph 0034).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the optical head structure as disclosed by Yoshida, the layering structure and quantum wells as disclosed by Valster, and the asymmetric nature of the quantum well as disclosed by Sundaram, the motivation being to produce a more intense and direct laser beam that is more easily controlled by the asymmetric quantum wells.

Regarding claim 3, Yoshida, Valster, and Sundaram disclose all of the limitations of claim 1 as discussed in the claim 1 rejection above. Valster further discloses that the semiconductor laser has a barrier layer which is also said indirect semiconductor (column 6, lines 21-27 – see especially "Separate Confinement Layers" in lines 24 and 25).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the optical head structure as disclosed by Yoshida, the layering structure and quantum wells as disclosed by Valster, and the asymmetric nature of the quantum well as disclosed by Sundaram, the motivation being to produce a more intense and direct laser beam.

Regarding claim 4, Yoshida, Valster, and Sundaram disclose all of the limitations of claim 1 as discussed in the claim 1 rejection above. Valster further discloses that said indirect semiconductor is made of an indirect semiconductor mixed crystal material (column 1, lines 15-24).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the optical head structure as disclosed by Yoshida, the layering structure and quantum wells as disclosed by Valster, and the asymmetric nature of the quantum well as disclosed by Sundaram, the motivation being to produce a more intense and direct laser beam.

Regarding claim 5, Yoshida, Valster, and Sundaram disclose all of the limitations of claim 1 as discussed in the claim 1 rejection above. Yoshida further discloses that

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the optical head is used for reproducing information from the medium (see page 1, paragraphs 0004).

Regarding claim 7, Yoshida, Valster, and Sundaram disclose all of the limitations of claim 1 as discussed in the claim 1 rejection above. Valster further discloses that the indirect semiconductor has an adjacent confinement structure (column 6, lines 21-27 – see especially "Separate Confinement Layers" in lines 24 and 25).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the optical head structure as disclosed by Yoshida, the layering structure and quantum wells as disclosed by Valster, and the asymmetric nature of the quantum well as disclosed by Sundaram, the motivation being to produce a more intense and direct laser beam.

Regarding claim 8, Yoshida, Valster, and Sundaram disclose all of the limitations of claim 1 as discussed in the claim 1 rejection above. Valster further discloses that the material of the indirect semiconductor is of an AlGaP (aluminum, gallium, and phosphor) group (column 6, lines 25-27 – InAlGaP read to be in AlGaP group).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the optical head structure as disclosed by Yoshida, the layering structure and quantum wells as disclosed by Valster, and the asymmetric nature of the quantum well as disclosed by Sundaram, the motivation being to produce a more intense and direct laser beam.

Regarding claim 14, Yoshida, Valster, and Sundaram disclose all of the limitations of claim 1 as discussed in the claim 1 rejection above. Yoshida further

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discloses that a d.c. drive is used for driving the semiconductor laser (page 6, paragraph 0061).

Regarding claim 18, Yoshida, Valster, and Sundaram disclose all of the limitations of claim 1 as discussed in the claim 1 rejection above. Yoshida further discloses an optical disc apparatus (page 3, paragraph 0024).

6. Claim 11 is rejected under 35 U.S.C. 103(a) as being unpatentable over Yoshida et al. (hereinafter Yoshida – US Doc. No. 2002/0024153 A1) in view of Valster et al. (hereinafter Valster – US Pat. No. 5,296,717) and further in view of Sundaram et a. (hereinafter Sundaram – US Doc. No. 2004/0195509 A1) and even further in view of Chapple-Sokol et al. (hereinafter Chapple – US Pat. No. 5,354,707).

Regarding claim 11, Yoshida, Valster, and Sundaram disclose all of the limitations of claim 1 as discussed in the claim 1 rejection above. Yoshida, Valster, and Sundaram all fail to distinctly disclose that the material of the indirect semiconductor is of a SiGe (silicon germanium) group.

Chapple discloses an indirect semiconductor structure in which the layers are made from the SiGe group (see column 3, lines 11-38 - read to be in the SiGe group).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the optical head structure as disclosed by Yoshida, the layering structure and quantum wells as disclosed by Valster, the asymmetric nature of the quantum well as disclosed by Sundaram, and the layer structure as disclosed by Chapple, the motivation being to produce a more intense and direct laser beam.

7. Claim 15 is rejected under 35 U.S.C. 103(a) as being unpatentable over Yoshida et al. (hereinafter Yoshida – US Doc. No. 2002/0024153 A1) in view of Valster et al. (hereinafter Valster – US Pat. No. 5,296,717) and further in view of Sundaram et a. (hereinafter Sundaram – US Doc. No. 2004/0195509 A1) and even further in view of Hayashi (US Pat. No. 6,394,655 B1).

Regarding claim 15, Yoshida, Valster, and Sundaram disclose all of the limitations of claim 1 as discussed in the claim 1 rejection above. Yoshida, Valster, and Sundaram all fail to distinctly disclose that the optical head comprises a multi-layer film reflector provided at an end face of a resonator.

Hayashi discloses that a reflective film is formed at one end face of a resonator in his semiconductor laser (see abstract).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the optical head structure as disclosed by Yoshida, the layering structure and quantum wells as disclosed by Valster, the asymmetric nature of the quantum well as disclosed by Sundaram, and the film and resonator as disclosed by Hayashi, the motivation being to produce a laser with improved transmission speed.

8. Claim 16 is rejected under 35 U.S.C. 103(a) as being unpatentable over Yoshida et al. (hereinafter Yoshida – US Doc. No. 2002/0024153 A1) in view of Valster et al. (hereinafter Valster – US Pat. No. 5,296,717) and further in view of Sundaram et a. (hereinafter Sundaram – US Doc. No. 2004/0195509 A1) and even further in view of Momoo et al. (hereinafter Momoo - US Pat. No. 6,741,538 B2).

Regarding claim 16, Yoshida, Valster, and Sundaram disclose all of the limitations of claim 1 as discussed in the claim 1 rejection above. Yoshida, Valster, and Sundaram all fail to distinctly disclose that the optical head comprises a waveband pass filter for limiting the wavelength of the light beam from the semiconductor laser to be less a half-value width of 2 nm.

Momoo discloses a semiconductor laser system that uses a band-pass filter, in order to limit the reflection and transmission of the light by the wavelength (see column 1, lines 46-48 – this filter can be set to any wavelength for the best mode of operation).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the optical head structure as disclosed by Yoshida, the layering structure and quantum wells as disclosed by Valster, the asymmetric nature of the quantum well as disclosed by Sundaram, and the band-pass filter as disclosed by Momoo, the motivation being in order to limit the reflection and transmission of the light by the wavelength.

9. Claim 17 is rejected under 35 U.S.C. 103(a) as being unpatentable over Yoshida et al. (hereinafter Yoshida – US Doc. No. 2002/0024153 A1) in view of Valster et al. (hereinafter Valster – US Pat. No. 5,296,717) and further in view of Sundaram et a. (hereinafter Sundaram – US Doc. No. 2004/0195509 A1) and even further in view of Brown (US Pat. No. 5,625,729).

Regarding claim 17, Yoshida, Valster, and Sundaram disclose all of the limitations of claim 1 as discussed in the claim 1 rejection above. Yoshida, Valster, and

Sundaram all fail to distinctly disclose that the optical head comprises a cooler for lowering the temperature of a light emitting part of the semiconductor laser.

Brown discloses a semiconductor laser with heat sinks or active coolers for lowering the temperature of the light emitting part of the laser during operation (see column 14, lines 20-34).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the optical head structure as disclosed by Yoshida, the layering structure and quantum wells as disclosed by Valster, the asymmetric nature of the quantum well as disclosed by Sundaram, and the cooler as disclosed by Brown in order to effectively avoid overheating the light emitting part of the laser.

## Allowable Subject Matter

10. Claims 9, 10, 12, and 13 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

See reasons for indicating allowable subject matter in the Office Action that was mailed on 4/4/2005.

#### Conclusion

11. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Adam R. Giesy whose telephone number is (571) 272-7555. The examiner can normally be reached on 8:00am- 5:30pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, William R. Korzuch can be reached on (571) 272-7589. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

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